

# Anthony Levi

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

163  
papers

5,815  
citations

39  
h-index

73  
g-index

183  
ext. papers

6,399  
ext. citations

3.6  
avg, IF

5  
L-index

#	Paper	IF	Citations
163	Supersymmetry with self-consistent Schrödinger-Boisson equations: finding partner potentials and breaking symmetry. <i>New Journal of Physics</i> , <b>2021</b> , 23, 063026	2.9	0
162	Graphene <b>2020</b> , 1-6		
161	Electron Transmission <b>2020</b> , 1-28		
160	Electron-Phonon Scattering in Semiconductors <b>2020</b> , 1-20		
159	The Lindhard dielectric function <b>2020</b> , 1-12		
158	Crystal systems and the reciprocal lattice <b>2020</b> , 1-4		
157	Permittivity and effective potential in the linear response approximation <b>2020</b> , 1-2		
156	Optimal heterostructure device design <b>2020</b> , 1-14		
155	The Boltzmann transport equation <b>2020</b> , 1-6		
154	Non-equilibrium electron scattering in n-type semiconductors <b>2020</b> , 1-32		
153	Semiclassical Electron Transport <b>2020</b> , 1-24		
152	Density of states and particle statistics <b>2020</b> , 1-20		
151	Toward Quantum Engineering <b>2020</b> , 1-10		
150	Expectation value $\langle \text{hd}(q, \mu) \rangle$ <b>2020</b> , 1-4		
149	Non-Equilibrium Minority Carrier Transport <b>2020</b> , 1-24		
148	Physical Values <b>2020</b> , 1-2		
147	Semiconductors and Quantized States <b>2020</b> , 1-34		

146	Behavioral regimes and long-lived emitter states in mesolasers. <i>Journal of Physics B: Atomic, Molecular and Optical Physics</i> , <b>2019</b> , 52, 245401	1.3	
145	Three-dimensional imaging of integrated circuits with macro- to nanoscale zoom. <i>Nature Electronics</i> , <b>2019</b> , 2, 464-470	28.4	42
144	Nanoscale x-ray imaging of circuit features without wafer etching. <i>Physical Review B</i> , <b>2017</b> , 95,	3.3	35
143	Quantification and control of non-Markovian evolution in finite quantum systems via feedback. <i>Physical Review A</i> , <b>2014</b> , 89,	2.6	3
142	Coherent control of non-Markovian photon-resonator dynamics. <i>Physical Review A</i> , <b>2014</b> , 90,	2.6	1
141	Optimal design of heterostructure tunnel diode with nonlinear current-voltage characteristic. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2012</b> , 44, 1503-1509	3	3
140	Gate tunable graphene-silicon Ohmic/Schottky contacts. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 223113	3.4	37
139	Graphene-silicon Schottky diodes. <i>Nano Letters</i> , <b>2011</b> , 11, 1863-7	11.5	397
138	Optimal design of a semiconductor heterostructure tunnel diode with linear current-voltage characteristic. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2011</b> , 44, 322-326	3	1
137	Ring resonator-based photonic microwave receiver modulator with picowatt sensitivity. <i>IET Optoelectronics</i> , <b>2011</b> , 5, 36-39	1.5	5
136	Quantum fluctuations and saturable absorption in mesoscale lasers. <i>Physical Review A</i> , <b>2011</b> , 83,	2.6	7
135	A Novel Formulation of the Adjoint Method in the Optimal Design of Quantum Electronic Devices. <i>SIAM Journal on Control and Optimization</i> , <b>2010</b> , 48, 3191-3223	1.9	10
134	Quantum fluctuations in very small laser diodes. <i>Physical Review A</i> , <b>2010</b> , 81,	2.6	11
133	Quantum fluctuations in small lasers. <i>Physical Review Letters</i> , <b>2009</b> , 102, 053902	7.4	19
132	Plasmonic excitations in tight-binding nanostructures. <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	15
131	Towards Quantum Engineering. <i>Proceedings of the IEEE</i> , <b>2008</b> , 96, 335-342	14.3	9
130	Electro-optic bistability in a LiNbO3 microdisk resonator. <i>IET Optoelectronics</i> , <b>2008</b> , 2, 111-114	1.5	
129	Optimal control of electromagnetic field using metallic nanoclusters. <i>New Journal of Physics</i> , <b>2008</b> , 10, 043017	2.9	15

128	Self-homodyne photonic microwave receiver architecture based on linear optical modulation and filtering. <i>Microwave and Optical Technology Letters</i> , <b>2008</b> , 50, 345-350	1.2	4
127	Design of resonators using materials with negative refractive index. <i>Journal of the Optical Society of America B: Optical Physics</i> , <b>2007</b> , 24, 2791	1.7	2
126	Optimization of aperiodic dielectric structures. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 034310	2.5	29
125	Synthesis of electron transmission in nanoscale semiconductor devices. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 013502	3.4	9
124	Electromagnetic response of broken-symmetry nanoscale clusters. <i>Physical Review Letters</i> , <b>2006</b> , 97, 036806	7.4	23
123	14.6-GHz LiNbO <sub>3</sub> /sub 3/ microdisk photonic self-homodyne RF receiver. <i>IEEE Transactions on Microwave Theory and Techniques</i> , <b>2006</b> , 54, 821-831	4.1	21
122	Applied Quantum Mechanics <b>2006</b> ,		41
121	Self-homodyne RF-optical LiNbO <sub>3</sub> microdisk receiver. <i>Solid-State Electronics</i> , <b>2005</b> , 49, 1428-1434	1.7	24
120	Synthesis for semiconductor device design. <i>Journal of Applied Physics</i> , <b>2005</b> , 98, 044508	2.5	1
119	Aperiodic nanophotonic design. <i>Journal of Applied Physics</i> , <b>2004</b> , 95, 1420-1426	2.5	17
118	Adaptive quantum design of atomic clusters. <i>Physical Review B</i> , <b>2004</b> , 69,	3.3	6
117	Adaptive design of excitonic absorption in broken-symmetry quantum wells. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 121-123	3.4	14
116	MAUI: enabling fiber-to-the-Processor with parallel multiwavelength optical interconnects. <i>Journal of Lightwave Technology</i> , <b>2004</b> , 22, 2043-2054	4	50
115	Accessing transmission-mode dispersion in super-prisms. <i>Solid-State Electronics</i> , <b>2003</b> , 47, 1369-1377	1.7	1
114	Polarization-dependent reflectivity from dielectric nanowires. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 996-998	3.4	14
113	Adaptive design of nanoscale dielectric structures for photonics. <i>Journal of Applied Physics</i> , <b>2003</b> , 94, 6065-6068	2.5	9
112	Active microdisk devices <b>2000</b> , 3947, 185		1
111	Wavelength switching in multi-cavity laser diodes. <i>Journal of Applied Physics</i> , <b>1998</b> , 84, 1805-1812	2.5	

110	A multistate external cavity laser diode. <i>Applied Physics Letters</i> , <b>1998</b> , 72, 2214-2216	3-4	1
109	Wavelength switching in multicavity lasers. <i>Applied Physics Letters</i> , <b>1997</b> , 71, 300-302	3-4	3
108	Throughput optimization for multimedia applications over high speed networks <b>1997</b> , 101-114		
107	Video broadcast using an optically controlled serially fed phased-array antenna <b>1996</b> , 2844, 258		2
106	Transient response of wavelength switching in multicavity mode-locked laser diodes. <i>Applied Physics Letters</i> , <b>1996</b> , 69, 3647-3649	3-4	5
105	The effect of scaling microlasers on modal noise. <i>Applied Physics Letters</i> , <b>1996</b> , 69, 3459-3461	3-4	
104	The spectrum of microdisk lasers. <i>Journal of Applied Physics</i> , <b>1996</b> , 80, 644-653	2-5	61
103	Transferred-electron induced current instabilities in heterojunction bipolar transistors. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 3319-3321	3-4	5
102	Polarization of lasing emission in microdisk laser diodes. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 1859-1861	3-4	14
101	Resonant modes and laser spectrum of microdisk lasers. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 2932-2934	3-4	57
100	Comparison of plasma chemistries for patterning InP-based laser structures. <i>Plasma Sources Science and Technology</i> , <b>1994</b> , 3, 19-24	3-5	5
99	InGaAs/GaAs quantum well lasers with dry-etched mirror passivated by vacuum atomic layer epitaxy. <i>Applied Physics Letters</i> , <b>1994</b> , 65, 1748-1750	3-4	4
98	Comparison of graded and abrupt junction In <sub>0.53</sub> Ga <sub>0.47</sub> As heterojunction bipolar transistors. <i>Applied Physics Letters</i> , <b>1994</b> , 64, 67-69	3-4	14
97	Forward delay in scaled Al <sub>0.48</sub> In <sub>0.52</sub> As/In <sub>0.53</sub> Ga <sub>0.47</sub> As heterojunction bipolar transistors. <i>Applied Physics Letters</i> , <b>1993</b> , 63, 2231-2233	3-4	4
96	Threshold characteristics of semiconductor microdisk lasers. <i>Applied Physics Letters</i> , <b>1993</b> , 63, 1310-1312	3-4	203
95	Wavelength dependence of T <sub>0</sub> in InGaAsP semiconductor laser diodes. <i>Applied Physics Letters</i> , <b>1993</b> , 62, 2009-2011	3-4	5
94	Direct observation of the electron spectral function in the integer and fractional quantum Hall regimes by resonant tunneling. <i>Physical Review B</i> , <b>1993</b> , 47, 16608-16611	3-3	12
93	Carrier pinning by mode fluctuations in laser diodes. <i>Applied Physics Letters</i> , <b>1993</b> , 62, 1454-1456	3-4	9

92	Room-temperature lasing action in In <sub>0.51</sub> Ga <sub>0.49</sub> P/In <sub>0.2</sub> Ga <sub>0.8</sub> As microcylinder laser diodes. <i>Applied Physics Letters</i> , <b>1993</b> , 62, 2021-2023	3.4	70
91	Forward transit delay in In/sub 0.53/Ga/sub 0.47/As heterojunction bipolar transistors with nonequilibrium electron transport. <i>IEEE Transactions on Electron Devices</i> , <b>1993</b> , 40, 1942-1949	2.9	7
90	Directional light coupling from microdisk lasers. <i>Applied Physics Letters</i> , <b>1993</b> , 62, 561-563	3.4	148
89	Vertical scaling in heterojunction bipolar transistors with nonequilibrium base transport. <i>Applied Physics Letters</i> , <b>1992</b> , 60, 460-462	3.4	34
88	On the temperature sensitivity of semiconductor lasers. <i>Applied Physics Letters</i> , <b>1992</b> , 60, 157-159	3.4	28
87	Temperature dependence of long wavelength semiconductor lasers. <i>Applied Physics Letters</i> , <b>1992</b> , 60, 1058-1060	3.4	28
86	Cavity formation in semiconductor lasers. <i>Applied Physics Letters</i> , <b>1992</b> , 61, 889-891	3.4	4
85	Nonlinear spectroscopy near half-gap in bulk and quantum well GaAs/AlGaAs waveguides. <i>Journal of Applied Physics</i> , <b>1992</b> , 71, 1927-1935	2.5	38
84	Whispering-gallery mode microdisk lasers. <i>Applied Physics Letters</i> , <b>1992</b> , 60, 289-291	3.4	1073
83	Single Crystal NiSi <sub>2</sub> /Si Interfaces: Fabrication, Structures, and Schottky Barrier Heights. <i>Materials Research Society Symposia Proceedings</i> , <b>1991</b> , 221, 71		2
82	Asymmetric line broadening in intracavity loss modulated quantum well distributed feedback lasers. <i>Applied Physics Letters</i> , <b>1991</b> , 58, 669-671	3.4	4
81	Ordered monolayer structures of boron in Si(111) and Si(100). <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>1991</b> , 9, 2269-2272	2.9	19
80	Large nonlinear phase shifts in low-loss Al <sub>x</sub> Ga <sub>1-x</sub> As waveguides near half-gap. <i>Applied Physics Letters</i> , <b>1991</b> , 59, 2558-2560	3.4	43
79	Electrical conduction in the Si(111):B-( $\sqrt{3} \times \sqrt{3}$ )R30 degrees/a-Si interface reconstruction. <i>Physical Review B</i> , <b>1991</b> , 43, 14711-14714	3.3	22
78	Low-threshold GaAs/AlGaAs quantum-well lasers grown by organometallic vapor-phase epitaxy using trimethylamine alane. <i>Journal of Applied Physics</i> , <b>1991</b> , 70, 432-435	2.5	16
77	Saturable absorption in intracavity loss modulated quantum well lasers. <i>Applied Physics Letters</i> , <b>1991</b> , 59, 16-18	3.4	12
76	Schottky-barrier inhomogeneity at epitaxial NiSi <sub>2</sub> interfaces on Si(100). <i>Physical Review Letters</i> , <b>1991</b> , 66, 72-75	7.4	173
75	Picosecond pump and probe spectroscopy utilizing freely propagating terahertz radiation. <i>Optics Letters</i> , <b>1991</b> , 16, 48-9	3	66

74	All-optical timing restoration using a hybrid time-domain chirp switch. <i>Optics Letters</i> , <b>1991</b> , 16, 1116-8	3	4
73	Log-periodic antennas for pulsed terahertz radiation. <i>Applied Physics Letters</i> , <b>1991</b> , 59, 262-264	3.4	37
72	Ultrahigh-Speed Bipolar Transistors. <i>Physics Today</i> , <b>1990</b> , 43, 58-64	0.9	15
71	Dynamic optoelectronic read/write memory. <i>Applied Physics Letters</i> , <b>1990</b> , 56, 1501-1503	3.4	1
70	Nonequilibrium electron transport in heterostructure bipolar transistors probed by magnetic field. <i>Applied Physics Letters</i> , <b>1990</b> , 56, 2660-2662	3.4	14
69	Direct observation of two-dimensional magnetopolarons in a resonant tunnel junction. <i>Physical Review Letters</i> , <b>1990</b> , 65, 235-238	7.4	64
68	Ultrafast coplanar air-transmission lines. <i>Applied Physics Letters</i> , <b>1990</b> , 57, 1123-1125	3.4	29
67	Dynamic and static response of multielectrode lasers. <i>Applied Physics Letters</i> , <b>1990</b> , 57, 968-970	3.4	20
66	Large-signal picosecond response of InGaAs/InP quantum well lasers with an intracavity loss modulator. <i>Applied Physics Letters</i> , <b>1990</b> , 56, 1629-1631	3.4	5
65	Si(100)-(2 $\times$ 1)boron reconstruction: Self-limiting monolayer doping. <i>Applied Physics Letters</i> , <b>1990</b> , 57, 2779-2781	3.4	51
64	Multielectrode quantum well laser for digital switching. <i>Applied Physics Letters</i> , <b>1990</b> , 56, 1095-1097	3.4	14
63	High index contrast mirrors for optical microcavities. <i>Applied Physics Letters</i> , <b>1990</b> , 57, 1387-1389	3.4	39
62	Wavelength switching in InGaAs/InP quantum well lasers. <i>Applied Physics Letters</i> , <b>1990</b> , 56, 122-124	3.4	13
61	Base doping limits in heterostructure bipolar transistors. <i>Applied Physics Letters</i> , <b>1990</b> , 56, 1460-1462	3.4	23
60	Electron transport in an AlSb/InAs/GaSb tunnel emitter hot-electron transistor. <i>Applied Physics Letters</i> , <b>1989</b> , 55, 1891-1893	3.4	12
59	AlAs/GaAs tunnel emitter bipolar transistor. <i>Applied Physics Letters</i> , <b>1989</b> , 54, 2250-2252	3.4	15
58	Tunneling in the presence of phonons: A solvable model. <i>Physical Review Letters</i> , <b>1989</b> , 62, 1683-1686	7.4	83
57	Very low threshold InGaAs/InGaAsP graded index separate confinement heterostructure quantum well lasers grown by atmospheric pressure metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , <b>1989</b> , 55, 2283-2285	3.4	47

56	Nonrandom doping and elastic scattering of carriers in semiconductors. <i>Applied Physics Letters</i> , <b>1989</b> , 54, 940-942	3-4	48
55	Pair-breaking description of the vortex-depinning critical field in YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7</sub> thin films. <i>Physical Review B</i> , <b>1989</b> , 40, 5243-5246	3-3	61
54	Numerical study of nonequilibrium electron transport in AlGaAs/GaAs heterojunction bipolar transistors. <i>Applied Physics Letters</i> , <b>1989</b> , 55, 250-252	3-4	16
53	Electrical response of superconducting YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-<math>\delta</math></sub> to light. <i>Applied Physics Letters</i> , <b>1989</b> , 54, 1175-1177	3-4	66
52	Bias-controlled intersubband wavelength switching in a GaAs/AlGaAs quantum well laser. <i>Applied Physics Letters</i> , <b>1989</b> , 55, 1382-1384	3-4	20
51	High-frequency study of nonequilibrium transport in heterostructure bipolar transistors. <i>Applied Physics Letters</i> , <b>1989</b> , 55, 1789-1791	3-4	15
50	High-field transport in GaAs transistors. <i>Applied Physics Letters</i> , <b>1989</b> , 54, 813-815	3-4	19
49	Near-ideal lateral scaling in abrupt Al <sub>0.48</sub> In <sub>0.52</sub> As/In <sub>0.53</sub> Ga <sub>0.47</sub> As heterostructure bipolar transistors prepared by molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>1989</b> , 54, 2333-2335	3-4	42
48	Voltage-controlled Q switching of InGaAs/InP single quantum well lasers. <i>Applied Physics Letters</i> , <b>1989</b> , 55, 1940-1942	3-4	11
47	Ion-beam-induced metal-insulator transition in YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-<math>\delta</math></sub> : A mobility edge. <i>Physical Review B</i> , <b>1989</b> , 39, 11599-11602	3-3	132
46	Ion beam thinning and polishing of YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7</sub> films. <i>Applied Physics Letters</i> , <b>1989</b> , 55, 1915-1917	3-4	42
45	Epitaxial NiSi <sub>2</sub> and CoSi <sub>2</sub> Interfaces. <i>NATO ASI Series Series B: Physics</i> , <b>1989</b> , 167-181		5
44	Origin of the excess capacitance at intimate Schottky contacts. <i>Physical Review Letters</i> , <b>1988</b> , 60, 53-56	7-4	175
43	Inelastic scattering of electrons traversing semiconductor heterojunctions. <i>Applied Physics Letters</i> , <b>1988</b> , 52, 236-238	3-4	9
42	GaInAs/GaInAsP/InP heterostructure bipolar transistors with very thin base (150 Å) grown by chemical beam epitaxy. <i>Applied Physics Letters</i> , <b>1988</b> , 53, 983-985	3-4	14
41	Controllable reduction of critical currents in YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-<math>\delta</math></sub> films. <i>Applied Physics Letters</i> , <b>1988</b> , 53, 1010-1012	3-4	95
40	Normal-state transport parameters of epitaxial thin films of YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-<math>\delta</math></sub> . <i>Physical Review B</i> , <b>1988</b> , 38, 2472-2476	3-3	78
39	Coreless defects and the continuity of epitaxial NiSi <sub>2</sub> /Si(100) thin films. <i>Applied Physics Letters</i> , <b>1988</b> , 52, 828-830	3-4	27

38	Summary Abstract: Hot-electron transport in the AlSb/InAs/GaSb double heterostructure prepared by molecular-beam epitaxy. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1988</b> , 6, 674		3
37	Preparation of superconducting thin films of calcium strontium bismuth copper oxides by coevaporation. <i>Applied Physics Letters</i> , <b>1988</b> , 52, 1828-1830	3-4	67
36	Ion-beam-induced destruction of superconducting phase coherence in YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-<math>\delta</math></sub> . <i>Physical Review B</i> , <b>1988</b> , 37, 3755-3758	3-3	96
35	Extreme nonequilibrium electron transport in heterojunction bipolar transistors. <i>Applied Physics Letters</i> , <b>1988</b> , 52, 2247-2249	3-4	19
34	Quantum reflections and inelastic scattering of electrons in semiconductor heterostructures. <i>Physical Review B</i> , <b>1988</b> , 38, 9843-9849	3-3	7
33	Unipolar Hot Electron Transistors. <i>Physica Scripta</i> , <b>1988</b> , T23, 227-231	2.6	3
32	Electroluminescence from the base of a GaAs/AlGaAs double heterojunction bipolar transistor. <i>Applied Physics Letters</i> , <b>1987</b> , 50, 98-100	3-4	17
31	Nonequilibrium electron transport in bipolar devices. <i>Applied Physics Letters</i> , <b>1987</b> , 51, 42-44	3-4	66
30	Room-temperature operation of hot-electron transistors. <i>Applied Physics Letters</i> , <b>1987</b> , 51, 984-986	3-4	99
29	Electron-transport dynamics in quantized intrinsic GaAs. <i>Physical Review B</i> , <b>1987</b> , 36, 9402-9405	3-3	20
28	Epitaxial yttrium silicide on (111) silicon by vacuum annealing. <i>Applied Physics Letters</i> , <b>1987</b> , 51, 311-313	3-4	45
27	Hot Electron Transistors Using Si/CoSi <sub>2</sub> . <i>Materials Research Society Symposia Proceedings</i> , <b>1987</b> , 102, 361		6
26	Hot Electron Transistors Using Si/CoSi <sub>2</sub> . <i>Materials Research Society Symposia Proceedings</i> , <b>1987</b> , 107, 259		7
25	Electron Transport Through Epitaxial Metal/Semiconductor Heterostructures. <i>Materials Research Society Symposia Proceedings</i> , <b>1986</b> , 77, 271		4
24	Epitaxial metal/semiconductor structures and their properties. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1986</b> , 4, 1435		37
23	States at epitaxial NiSi <sub>2</sub> /Si heterojunctions studied by deep-level transient spectroscopy and hydrogenation. <i>Physical Review B</i> , <b>1986</b> , 34, 4415-4418	3-3	23
22	Control of a natural permeable CoSi <sub>2</sub> base transistor. <i>Applied Physics Letters</i> , <b>1986</b> , 48, 635-637	3-4	122
21	Schottky-barrier heights of single-crystal NiSi <sub>2</sub> on Si(111): The effect of a surface p-n junction. <i>Physical Review B</i> , <b>1986</b> , 33, 7077-7090	3-3	77

20	Dynamics of injected electron cooling in GaAs. <i>Applied Physics Letters</i> , <b>1986</b> , 48, 1365-1367	3-4	7
19	Growth of strained-layer semiconductor-metal-semiconductor heterostructures. <i>Applied Physics Letters</i> , <b>1986</b> , 48, 1264-1266	3-4	39
18	Ballistic injection devices in semiconductors. <i>Applied Physics Letters</i> , <b>1986</b> , 48, 1609-1611	3-4	42
17	Base transport dynamics in a heterojunction bipolar transistor. <i>Applied Physics Letters</i> , <b>1986</b> , 49, 1481-1483	3-4	29
16	Hot Electron Transistors. <i>Springer Series in Electrophysics</i> , <b>1986</b> , 19-23		
15	Injected-hot-electron transport in GaAs. <i>Physical Review Letters</i> , <b>1985</b> , 55, 2071-2073	7-4	196
14	Transistor action in Si/CoSi <sub>2</sub> /Si heterostructures. <i>Applied Physics Letters</i> , <b>1985</b> , 47, 151-153	3-4	163
13	Hot-electron spectroscopy of GaAs. <i>Physical Review Letters</i> , <b>1985</b> , 54, 1570-1572	7-4	132
12	Magnetic field dependence of hot-electron transport in GaAs. <i>Applied Physics Letters</i> , <b>1985</b> , 47, 964-966	3-4	11
11	Phonon Structure of Amorphous Germanium by Inelastic Electron Tunnelling Spectroscopy <b>1985</b> , 913-916		
10	Phonon structure of amorphous germanium by inelastic electron tunnelling spectroscopy. <i>Journal of Physics C: Solid State Physics</i> , <b>1984</b> , 17, 1643-1653		9
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2	Gigabyte/s data communications with the POLO parallel optical link	19
1	Essential Classical Mechanics for Device Physics	10